

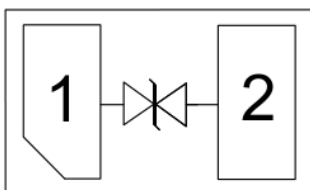
Features

- ◆ Ultra small package: 0.6x0.3x0.3mm
- ◆ Ultra low capacitance: 0.35pF typical
- ◆ Ultra low leakage: nA level
- ◆ Low operating voltage: 5V
- ◆ Low clamping voltage
- ◆ 2-pin leadless package
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 20\text{kV}$
 - Contact discharge: $\pm 15\text{kV}$
 - IEC61000-4-5 (Lightning) 4A (8/20 μs)
- ◆ RoHS Compliant

Description

The ESDA5B0M0D1 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high - speed data lines. The ESDA5B0M0D1 has an ultra-low capacitance with a typical value at 0.35pF, and complies with the IEC -4-2 (ESD) standard with $\pm 15\text{kV}$ air and $\pm 8\text{kV}$ contact discharge. It is assembled into an ultra-small 0.6x0.3x0.3mm lead-free 0201 package. The small size, ultra-low capacitance and high ESD surge protection make ESDA5B0M0D1 an ideal choice to protect cell phone , digital video interfaces and other high speed ports.

Circuit Diagram



Applications

- ◆ Smart phones
- ◆ Display Ports
- ◆ MDDI Ports
- ◆ USB Ports
- ◆ Digital Video Interface (DVI)
- ◆ PCI Express and Serial SATA Ports

Absolute Maximum Ratings : ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

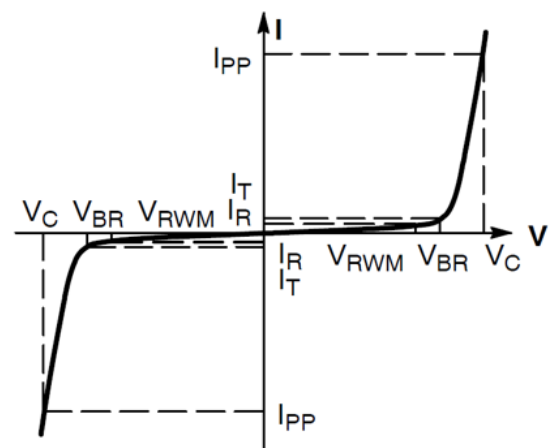
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	80	W
Peak Pulse Current (8/20 μs)	IPP	4	A
ESD per IEC 61000-4-2 (Air)	VESD	± 20	kV
ESD per IEC 61000-4-2 (Contact)		± 15	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics : ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				5.0	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	6.0		9.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 5.0\text{V}$			0.1	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ (8 / 20 μs pulse)			12	V
Clamping Voltage	V_C	$I_{PP} = 4\text{A}$ (8 / 20 μs pulse)			20	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$		0.35	0.5	pF

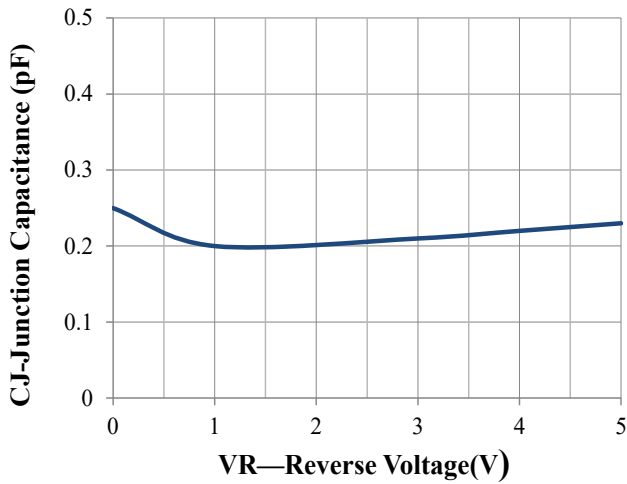
Portion Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}

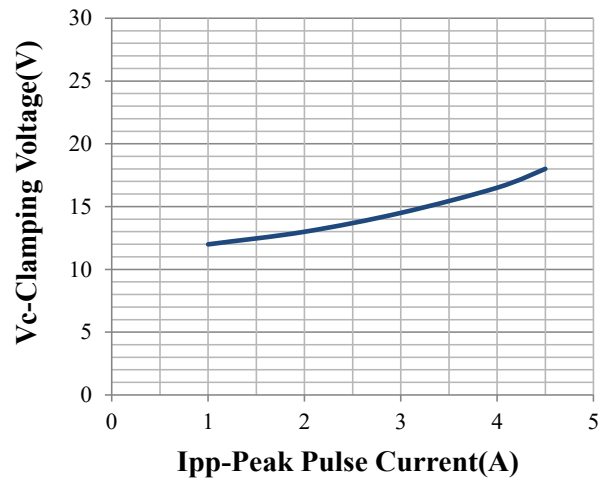


Bi-Directional TVS

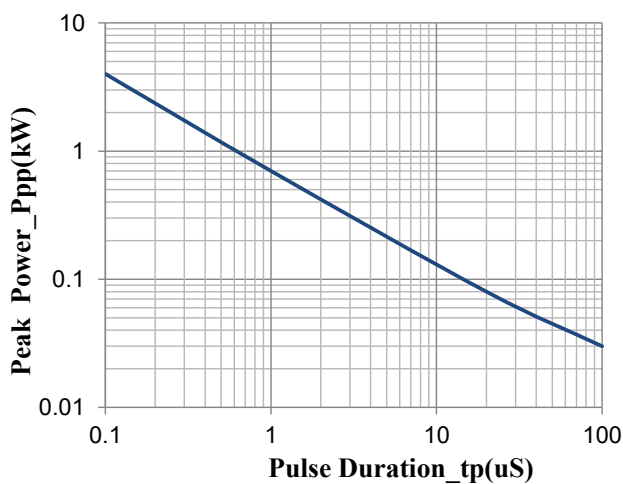
Typical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)



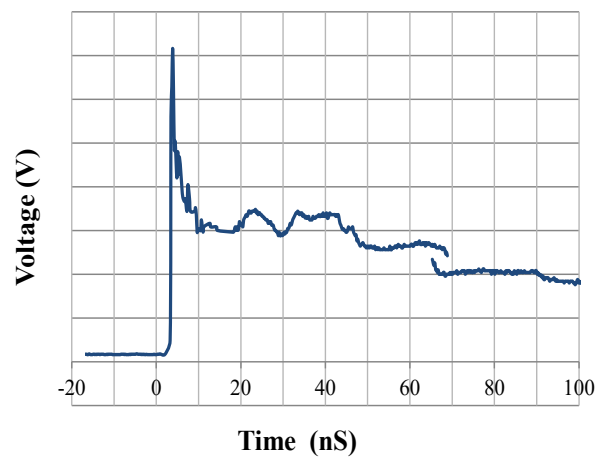
Junction Capacitance vs. Reverse Voltage



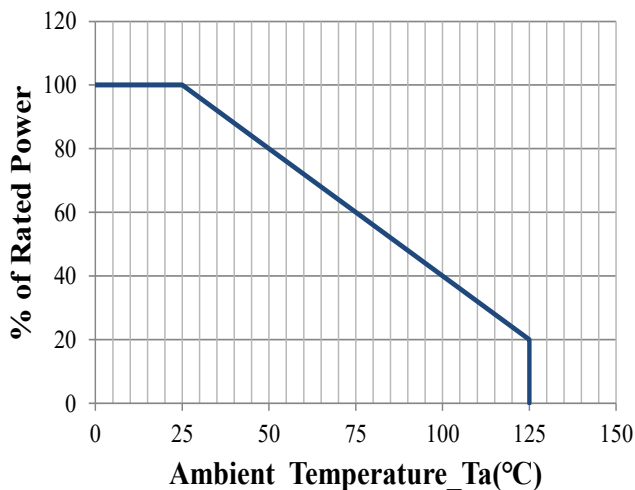
Clamping Voltage vs. Peak Pulse Current



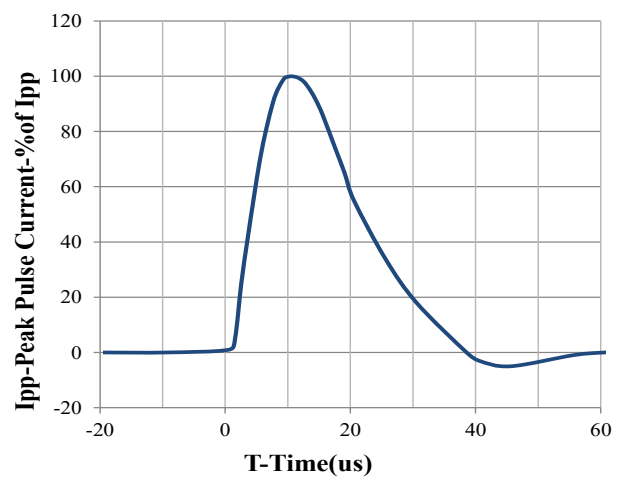
Peak Pulse Power vs. Pulse Time



IEC61000-4-2 Pulse Waveform



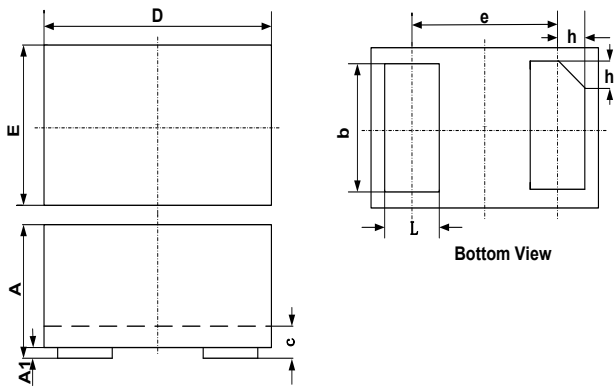
Power Derating Curve



8 / 20us Pulse Waveform

Package Dimension

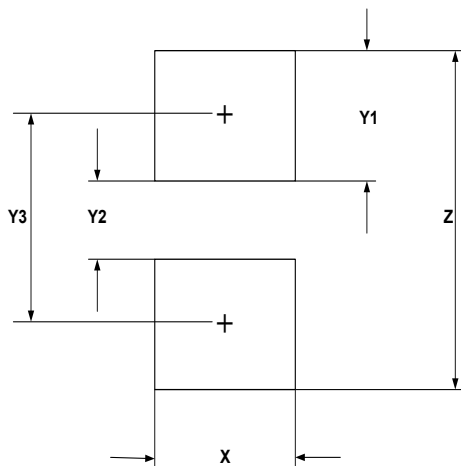
DFN0603-2(0201) Package Outline



Bottom View

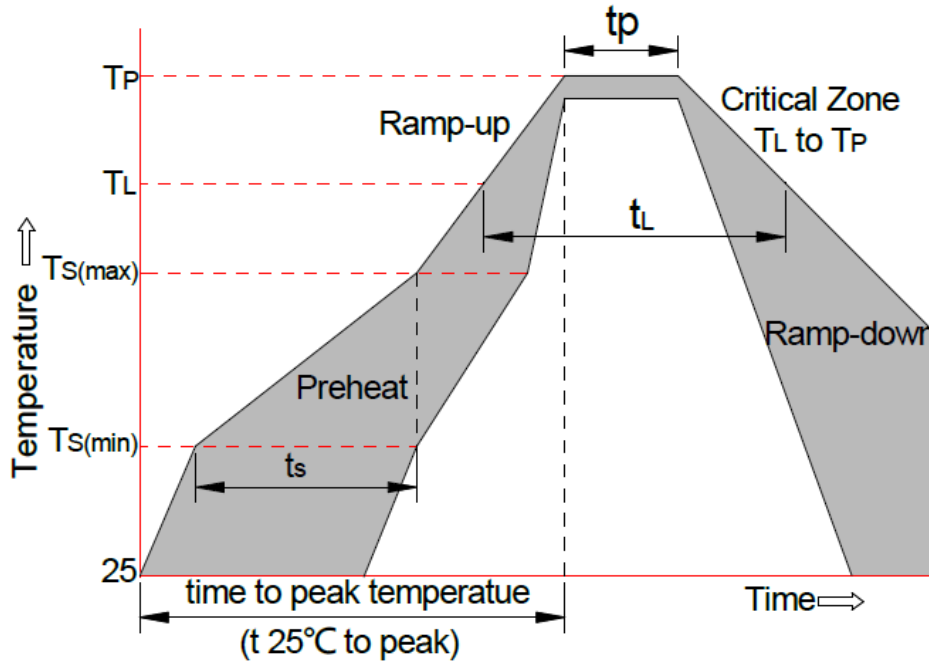
SYM	DIMENSIONS		
	MILLIMETERS		
	MIN	NOM	MAX
A	0.230		0.330
A1	0.000	0.020	0.050
b	0.215	0.245	0.275
c	0.120	0.150	0.180
D	0.550	0.600	0.650
e	0.355 BSC		
E	0.250	0.300	0.350
L	0.160	0.190	0.220
h	0.079 BSC		

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.30	0.012
Y1	0.25	0.010
Y2	0.15	0.006
Y3	0.40	0.016
Z	0.65	0.026

Soldering Parameters



Reflow Condition		Pb-Free Assembly
Pre-heat	-Temperature Min (Ts (min))	+150°C
	-Temperature Max (Ts (max))	+200°C
	-Time (Min to Max) (ts)	60-180 secs
Average ramp up rate(Liquid us Temp (TL) to peak)		3°C/sec. Max
Ts (max) to TL-Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature (TL) (Liquid us)	+217°C
	-Temperature (tL)	60-150 secs
Peak Temp (Tp)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (tp)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
xTime 25°C to Peak Temp (Tp)		8 min. Max
Do not exceed		+260°C